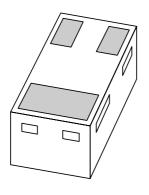
DISCRETE SEMICONDUCTORS

DATA SHEET



BC857M series PNP general purpose transistors

Product data sheet Supersedes data of 2003 Jul 15



PNP general purpose transistors

BC857M series

FEATURES

- Leadless ultra small plastic package (1 mm × 0.6 mm × 0.5 mm)
- Board space 1.3 × 0.9 mm
- Power dissipation comparable to SOT23.

APPLICATIONS

- General purpose small signal DC
- Low and medium frequency AC applications
- Mobile communications, digital (still) cameras, PDAs, PCMCIA cards.

DESCRIPTION

PNP general purpose transistor in a SOT883 leadless ultra small plastic package.

NPN complement: BC847M series.

MARKING

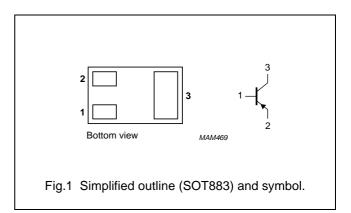
TYPE NUMBER	MARKING CODE
BC857AM	D1
BC857BM	D2
BC857CM	D3

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-45	V
I _C	collector current (DC)	-100	mA
I _{CM}	peak collector current	-200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
TIPE NUMBER			VERSION
BC857AM	_	Leadless ultra small plastic package; 3 solder lands; body	SOT883
BC857BM		1.0 x 0.6 x 0.5 mm	
BC857CM			

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V_{CEO}	collector-emitter voltage	open base	_	-45	V
V_{EBO}	emitter-base voltage	open collector	_	-5	٧
I _C	collector current (DC)		_	-100	mA
I_{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
		note 1	_	250	mW
		note 2	_	430	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μ m copper strip line.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
		note 1	500	K/W
		note 2	290	K/W

Notes

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm².

PNP general purpose transistors

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$			
	BC857AM		125	250	
	BC857BM		220	475	
	BC857CM		420	800	
V _{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	-	-820	mV
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-200	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note } 1$	_	-400	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	2.5	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	100	_	MHz
F	noise figure	$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$	_	10	dB

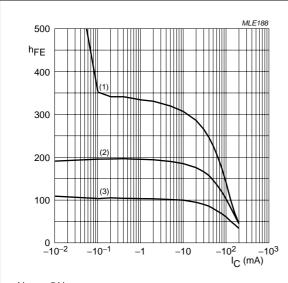
Note

^{1.} Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

PNP general purpose transistors

BC857M series

GRAPHICAL INFORMATION BC857AM



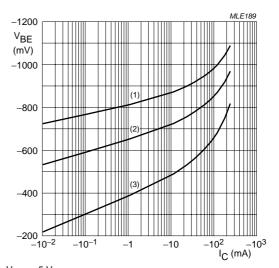
 $V_{CE} = -5 V.$

(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain; typical values.



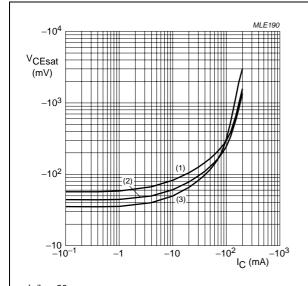
 $V_{CE} = -5 \text{ V}.$

(1) $T_{amb} = -55 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



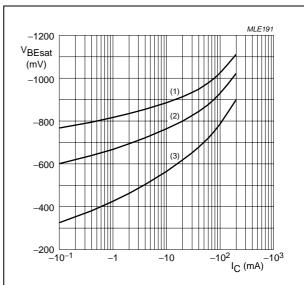
 $I_{\rm C}/I_{\rm B}=20.$

(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

(1) $T_{amb} = -55 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

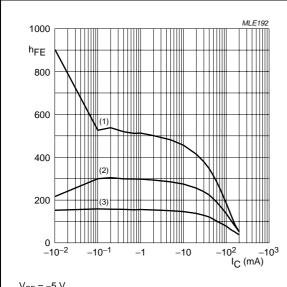
(3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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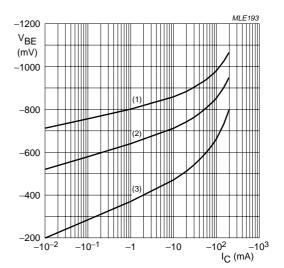
GRAPHICAL INFORMATION BC857BM



 $V_{CE} = -5 V.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

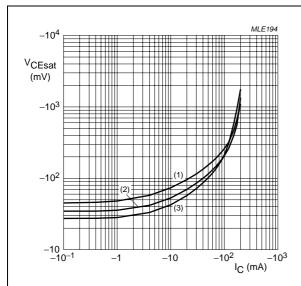
Fig.6 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

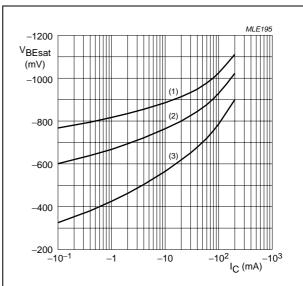
Fig.7 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

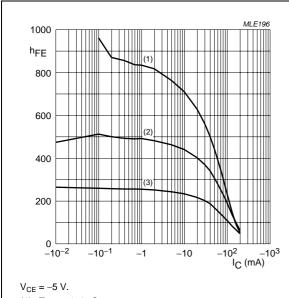
- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

PNP general purpose transistors

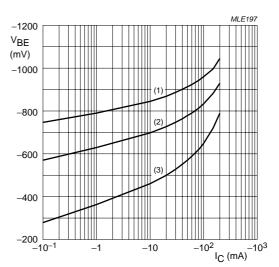
BC857M series

GRAPHICAL INFORMATION BC857CM



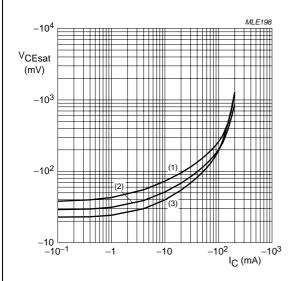
- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.10 DC current gain; typical values.



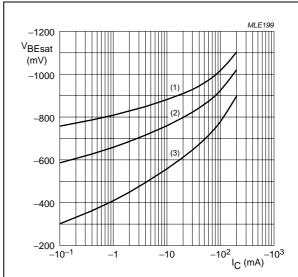
- $V_{CE} = -5 \text{ V}.$
- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.11 Base-emitter voltage as a function of collector current; typical values.



- $I_{\rm C}/I_{\rm B} = 20.$
- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



- $I_{\rm C}/I_{\rm B} = 20.$
- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

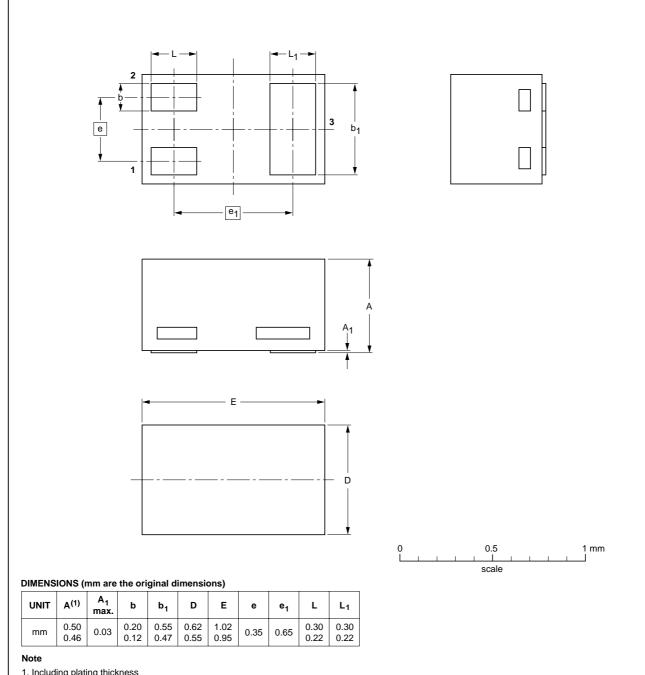
PNP general purpose transistors

BC857M series

PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



1. Including plating thickness

OUTLINE	UTLINE REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			03-02-05 03-04-03

PNP general purpose transistors

BC857M series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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